

TECHNICAL DATA DATA SHEET D0043 REV. B

SILICON SCHOTTKY RECTIFIER DIE

Applications:

• Switching Power Supply • Converters • Free-Wheeling Diodes • Polarity Protection Diode

Features:

- Ultra low Reverse Leakage Current
- Soft Reverse Recovery at Low and High Temperature
- Very Low Forward Voltage Drop
- Low Power Loss, High Efficiency
- High Surge Capacity
- Guard Ring for Enhanced Durability and Long Term Reliability
- Guaranteed Reverse Avalanche Characteristics
- Electrically / Mechanically Stable during and after Packaging

Maximum Ratings:

Characteristics	Symbol	Condition	Min.	Max.	Units
Working Peak Reverse Voltage	VRWM	I _R = 1 μA, T _J = 25 °C	50	-	V
Non-repetitive Peak Reverse Voltage	VRSM	I _R = 10 μA, T _J = 25 °C	70	-	V
Average Forward Current	I _{F(AV)}	50% duty cycle, rectangular wave form	-	1	mA
Junction Temperature	TJ	-	-55	125	°C
Storage Temperature	T _{stg}	-	-55	150	°C

Electrical Characteristics:

Characteristics	Symbol	Condition	Max.	Units
Forward Voltage Drop	V _{F1}	@ 1mA, Pulse, TJ = 25 °C	0.41	V
		@ 15mA, Pulse, T」 = 25 °C	1.00	v
Reverse Current	I _{R1}	$@V_R = 50V$, Pulse,	200	nA
		T _J = 25 °C		
Junction Capacitance	CT	@V _R = 0V, T _C = 25 °C	2	pF
		f _{SIG} = 1MHz,		
		V _{SIG} = 50mV (p-p)		

http://www.smc-diodes.com - sales@ smc-diodes.com •



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Mechanical Dimensions: In mil





1C5711

Bottom side metalization Cr/Ag/Au-5.2kÅ nominal Top side metalization Ti/Ni/Au-15kÅ nominal Bottom side is cathode, top side is anode

1C5711AG

Bottom side metalization Ti/Ni/Au-4kÅ minimum Top side metalization Ti/Al-25kÅ minimum Bottom side is cathode, top side is anode

Chip	Α	В	С
1C5711	15.0 ± 2.0	5.0 ± 1.0	11.0 ± 2.0
1C5711AG	15.0 ± 2.0	5.0 ± 1.0	10.0 ± 2.0

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